

ETCHING SOLUTION COMPOSITION

ABSTRACT

Provided is an etching solution composition that can have both a higher etch selectivity of silicon nitride and a
5 reduction in the deposition of silica on the surface of silicon oxide. An inorganic acid-based etching solution composition for selectively etching away silicon nitride from a semiconductor containing silicon nitride and silicon oxide, the etching solution composition comprising: (a) an etch
10 inhibitor that reduces etching of silicon oxide; and (b) a deposition inhibitor that reduces deposition of silica on a surface of silicon oxide.

[No Available Figure]